

5 A High Voltage Schottky Barrier Rectifier

DESCRIPTION

In Microsemi's new Powermite3[®] SMT package, these high efficiency ultrafast rectifiers offer the power handing capabilities previously found only in much larger packages. They are ideal for SMD applications that operate at high frequencies.

In addition to its size advantages, Powermite3® package features include a full metallic bottom that eliminates the possibility of solder flux entrapment during assembly, and a unique locking tab acts as an integral heat sink. Its innovative design makes this device ideal for use with automatic insertion equipment.

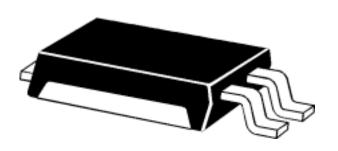
IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

ABSOLUTE MAXIMUM RATINGS AT 25° C (UNLESS OTHERWISE SPECIFIED)

(UNLESS OTHERW	ISE SPEC	IFIED)	
Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	V
RMS Reverse Voltage	V _{R (RMS)}	70	V
Average Rectified Output Current	Io	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine wave Superimposed on Rated Load@ T _c =80 °C	I _{FSM}	100	А
Storage Temperature	T stg	-65 to +150	ô
Operating Temperature	Тор	-65 to +125	°C

THERMAL CHARACTERISTICS (UNLESS OTHERWISE SPECIFIED) Thermal Resistance Junction-to Bottom Rja (1) 2.5 °C/Watt

(1) When Mounted on PC board with 2 ounce copper pattern.



KEY FEATURES

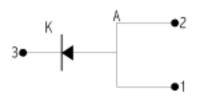
- High power surface mount package.
- Guard Ring die construction for transient protection.
- Silicon Schottky rectifiers no reverse voltage recovery.
- Internal heat sink locking tabs
- Low forward voltage.
- Full metallic bottom eliminates flux entrapment
- Compatible with automatic insertion equipment
- Low profile-maximum height of 1mm supplied in 16 mm tape reel- 5000 units/ 13" reel.

APPLICATIONS/BENEFITS

- Switching and Regulating Power Supplies.
- Charge Pump Circuits.
- Reduces reverse recovery loss due to low I_{RM}.
- Small foot print

 190 X 300 mils

 1:1 Actual size



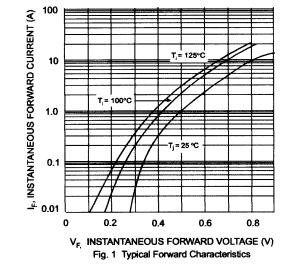
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ELECTRICAL PARAMETERS @ 25°C (unless otherwise specified)							
Parameter	Symbol	Conditions	Min	Тур.	Max	Units	
Forward Voltage (Note 1)		$I_F = 5 \text{ A}$, $T_i = 25 ^{\circ}\text{C}$		0.75	0.81		
Torward Vollago (Noto 1)	V_{Fm}	$I_F = 5 \text{ A}$, $T_j = 125 {}^{\circ}\text{C}$		0.58	0.64	V	
		$I_F = 10 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ $I_F = 10 \text{ A}$, $T_j = 125 ^{\circ}\text{C}$		0.84 0.67	0.90 0.73		
Reverse Break Down Voltage (Note 1)	V_{BR}	I _R = 0.2 mA	100			V	
Reverse Current (Note1)	I _{rm}	$V_R = 100V, T_j = 25^{\circ}C$ $V_R = 100V, T_j = 125^{\circ}C$		15 10	200 20	μA mA	
Capacitance	Ст	$V_R = 4 \text{ V}; \text{ F} = 1 \text{ MH}_Z$		150		pF	

Note: 1 Short duration test pulse used to minimize self – heating effect.



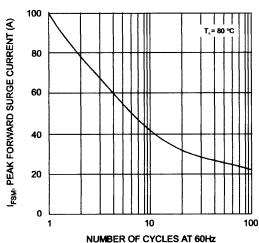
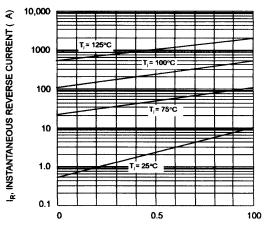
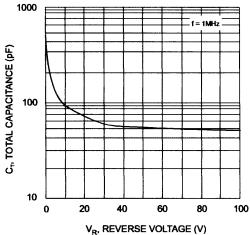


Fig. 3 Max Non-Repetitive Peak forward Surge Current



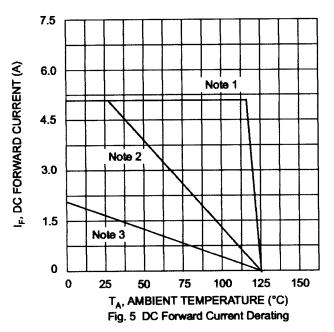
V_R, INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics

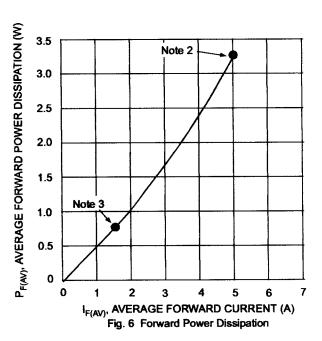


V_R, REVERSE VOLIAGE (V) Fig. 4 Typical Capacitance vs. Reverse Voltage



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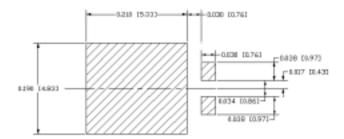




Notes:

- 1. $T_A = T_{SOLDERING\ POINT}$, $R_{\theta JS} = 2.7^{\circ}\text{C/W}$, $R_{\theta SA} = 0^{\circ}\text{C/W}$.
- 2. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0". Reus in range of 20-40°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R_{MA} in range of 100-140°C/W.

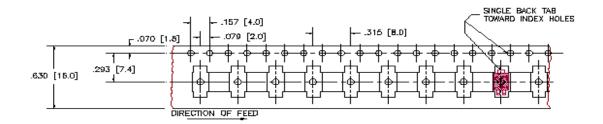
PAD LAYOUT



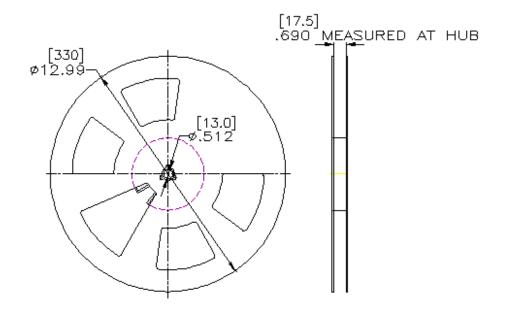


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16 mm TAPE



13 INCH REEL



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